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To:	Examiner George C. Eckert II	From:	Leslie S. Szivos, Ph.D.
Fax:	703 872-9306	Pages:	7 Including Cover Sheet
Phone:		Date:	1/28/2005
Re:	US Application No. 10/688,692 Filing Date: October 17, 2003 Docket No. YOR920030156US1 (16644)	CC:	

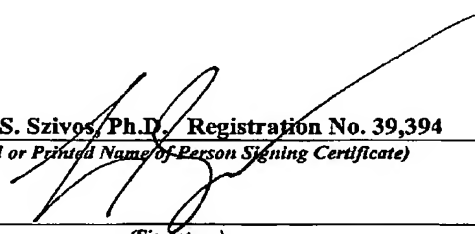
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Attached hereto is:

1. Response Under 37 C.F.R. §1.111 & §1.143
2. Amendment Transmittal (in duplicate)
3. Certificate of Facsimile

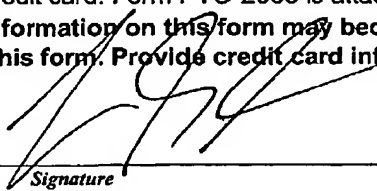
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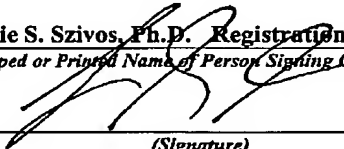
CERTIFICATE OF TRANSMISSION BY FACSIMILE (37 CFR 1.8)			Docket No.
Applicant(s): Kern Rim			YOR920030156US1 (16644)
Application No. 10/688,692	Filing Date October 17, 2003	Examiner George C. Eckert II	Group Art Unit 2815
Invention: DOUBLE SILICON-ON-INSULATOR (SOI) METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTOR (MOSFET) STRUCTURES			
<p>I hereby certify that this <u>Response Under 37 C.F.R. §1.111 & §1.143</u> (Identify type of correspondence) is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. <u>703 872-9306</u>) on <u>January 28, 2005</u> (Date)</p> <p><u>Leslie S. Szivos, Ph.D. Registration No. 39,394</u> (Typed or Printed Name of Person Signing Certificate)</p> <p> (Signature)</p>			
<p>Note: Each paper must have its own certificate of mailing.</p>			

P18/REV02

JAN 28 2005

TRANSMITTAL LETTER (General - Patent Pending)				Docket No. YOR920030156US1 (16644)	
In Re Application Of: Kern Rim					
Application No. 10/688,692	Filing Date 10/17/03	Examiner George C. Eckert II	Customer No. 23389	Group Art Unit 2815	Confirmation No. 2375
Title: DOUBLE SILICON-ON-INSULATOR (SOI) METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTOR (MOSFET) STRUCTURES					
<u>COMMISSIONER FOR PATENTS:</u>					
Transmitted herewith is: Response Under 37 C.F.R. §1.111 & §1.143					
in the above identified application.					
<input checked="" type="checkbox"/> No additional fee is required.					
<input type="checkbox"/> A check in the amount of _____ is attached.					
<input checked="" type="checkbox"/> The Director is hereby authorized to charge and credit Deposit Account No. 50-0510/IBM as described below.					
<input type="checkbox"/> Charge the amount of _____					
<input checked="" type="checkbox"/> Credit any overpayment.					
<input checked="" type="checkbox"/> Charge any additional fee required.					
<input type="checkbox"/> Payment by credit card. Form PTO-2038 is attached.					
WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.					
 _____ Signature			Dated: January 28, 2005		
Leslie S. Szivos, Ph.D. Registration No. 39,394					
<div style="border-bottom: 1px solid black; margin-bottom: 5px;">I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to the "Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450" [37 CFR 1.8(a)] on</div> <div style="border-bottom: 1px solid black; margin-bottom: 5px; text-align: center;">(Date)</div> <div style="border-bottom: 1px solid black; margin-bottom: 5px; text-align: center;">Signature of Person Mailing Correspondence</div> <div style="border-bottom: 1px solid black; margin-bottom: 5px; text-align: center;">Typed or Printed Name of Person Mailing Correspondence</div>					
CC:					

P16A/REV03

CERTIFICATE OF TRANSMISSION BY FACSIMILE (37 CFR 1.8)			Docket No.
Applicant(s): Kern Rim			YOR920030156US1 (16644)
Application No. 10/688,692	Filing Date October 17, 2003	Examiner George C. Eckert II	Group Art Unit 2815
Invention: DOUBLE SILICON-ON-INSULATOR (SOI) METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTOR (MOSFET) STRUCTURES			
<p>I hereby certify that this <u>Response Under 37 C.F.R. §1.111 & §1.143</u> (Identify type of correspondence) is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. <u>703 872-9306</u>) on <u>January 28, 2005</u> (Date)</p> <p><u>Leslie S. Szivos, Ph.D. Registration No. 39,394</u> (Typed or Printed Name of Person Signing Certificate)</p> <p><u></u> (Signature)</p> <p>Note: Each paper must have its own certificate of mailing.</p>			

P18/REV02

**TRANSMITTAL LETTER
(General - Patent Pending)**Docket No.
YOR920030156US1 (16644)In Re Application Of: **Kern Rim**

Application No.	Filing Date	Examiner	Customer No.	Group Art Unit	Confirmation No.
10/688,692	10/17/03	George C. Eckert II	23389	2815	2375

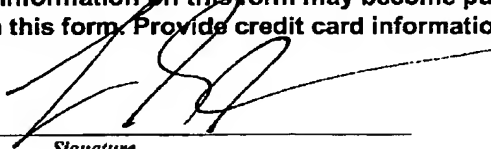
Title: **DOUBLE SILICON-ON-INSULATOR (SOI) METAL OXIDE SEMICONDUCTOR
FIELD EFFECT TRANSISTOR (MOSFET) STRUCTURES****COMMISSIONER FOR PATENTS:**

Transmitted herewith is:

Response Under 37 C.F.R. §1.111 & §1.143

in the above identified application.

- ☒ No additional fee is required.
- ☐ A check in the amount of _____ is attached.
- ☒ The Director is hereby authorized to charge and credit Deposit Account No. **50-0510/IBM** as described below.
- ☐ Charge the amount of _____
- ☒ Credit any overpayment.
- ☒ Charge any additional fee required.
- ☐ Payment by credit card. Form PTO-2038 is attached.

WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.

Signature

Dated: **January 28, 2005****Leslie S. Szivos, Ph.D.
Registration No. 39,394**

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to the "Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450" [37 CFR 1.8(a)] on

(Date)

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P16A/REV03

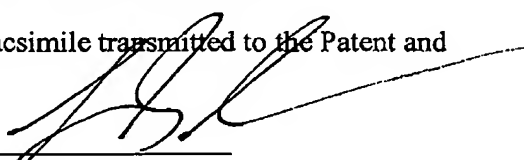
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**RECEIVED
CENTRAL FAX CENTER****Applicant(s):** Kern Rim, et al.**Examiner:** George C. Eckert II**JAN 28 2005****Serial No:** 10/688,692**Art Unit:** 2815**Filed:** October 17, 2003**Docket:** YOR920030125US1 (16644)**Dated:** January 28, 2005**For:** DOUBLE SILICON-ON-INSULATOR (SOI) METAL OXIDE SEMICONDUCTOR
FIELD EFFECT TRANSISTOR (MOSFET) STRUCTURES**Confirmation No:** 2375Mail Stop: Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450**RESPONSE UNDER 37 C.F.R. §§1.111 AND 1.143**

Sir:

In response to the Office Action dated January 12, 2005, applicants provisionally elect, without traverse, the subject matter of Group I, i.e., Claims 1-9 for continued prosecution in the above-identified patent application.

CERTIFICATION OF FACSIMILE TRANSMISSION

I hereby certify that this paper is being facsimile transmitted to the Patent and Trademark Office on the date shown below.

Dated: January 28, 2005
Leslie S. Szivos, Ph.D.

REMARKS

Favorable consideration and allowance of the claims of the present application are respectfully requested.

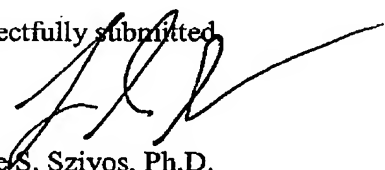
In the present Official Action, Claims 1-20, which are present in the above-captioned application, have been subjected to a restriction under 35 U.S.C. §121 as follows:

- I. Claims 1-9, drawn to an SOI device, classified in Class 257, subclass 347,
and
- II. Claims 10-20, drawn to a method of making a semiconductor device,
classified in Class 438, subclass 149.

As indicated, and in order to be fully responsive to the restriction requirement imposed in the present Official Action, applicants provisionally elect, without traverse, to prosecute the subject matter of Group I, i.e., Claims 1-9, and reserve the right to file one or more divisional applications directed to the non-elected subject matter in this application, i.e., Claims 10-20.

Wherefore, consideration and allowance of the claims of the present application are respectfully requested.

Respectfully submitted,


Leslie S. Szivos, Ph.D.
Registration No. 39,394

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